Special Issue

Electrical Characterization, Modeling and Simulation of CMOS Memory Devices

Message from the Guest Editor

This Special Issue aims to present studies on new materials and architectures for memory devices, conducted using methods of electrical characterization, modeling and device simulation and focused on consolidated themes such as non-volatile NAND flash and discrete-trap memories. Technological options for the near future, such as resistive RAM memories and one-transistor (1T)- and MIMCAP-based DRAMs, will also be considered.

- CMOS memory devices
- Device fabrication
- Modeling and numerical simulation
- Electrical material and device characterization
- One transistor (1T)-based DRAMs
- Metal-insulator-metal capacitors (MIMCAPs)
- Resistive memories (Re-RAMs)
- NAND flash memories
- Discrete-trap memories

Please click here to find information!
Welcome to contribute!

Guest Editor

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Deadline for manuscript submissions

closed (1 April 2022)

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About the Journal

Message from the Editor-in-Chief

Electronics is a multidisciplinary journal designed to appeal to a diverse audience of research scientists, practitioners, and developers in academia and industry. The journal is devoted to fast publication of latest technological breakthroughs, cutting-edge developments, and timely reviews of current and emerging technologies related to the broad field of electronics. Experimental and theoretical results are published as regular peer-reviewed articles or as articles within Special Issues guest-edited by leading experts in selected topics of interest.

Editor-in-Chief

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manuscripts are peer-reviewed and a first decision is provided to authors approximately 16.8 days after submission; acceptance to publication is undertaken in 2.4 days (median values for papers published in this journal in the first half of 2025).

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